

**100V(D-S) N-Channel Enhancement Mode Power MOS FET**

**General Features**

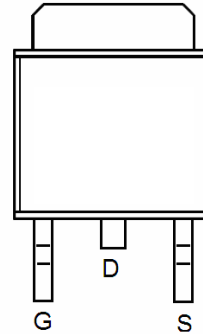
- $V_{DS}=100V, I_D=17A$   
 $R_{DS(ON)} < 70m\Omega @ V_{GS}=10V$  (Typ:56m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability



**Lead Free**

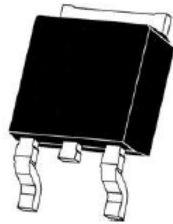
**Application**

- Power switching application
- Hard switched and high frequency circuits

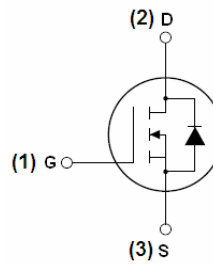


**Marking and pin assignment**

**PIN Configuration**



**TO-252-2L top view**



**Schematic diagram**

**Package Marking and Ordering Information**

| Device Marking | Device   | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| MSN1017D       | MSN1017D | TO-252-2L      | -         | -          | -        |

**Absolute Maximum Ratings ( $T_C=25^\circ C$  unless otherwise noted)**

| Parameter   | Symbol             | Limit      | Unit       |
|---|--------------------|------------|------------|
| Drain-Source Voltage                              | $V_{DS}$           | 100        | V          |
| Gate-Source Voltage                               | $V_{GS}$           | $\pm 20$   | V          |
| Drain Current-Continuous                          | $I_D$              | 17         | A          |
| Drain Current-Continuous( $T_C=100^\circ C$ )     | $I_D(100^\circ C)$ | 12         | A          |
| Pulsed Drain Current                              | $I_{DM}$           | 60         | A          |
| Maximum Power Dissipation                         | $P_D$              | 55         | W          |
| Single pulse avalanche energy <sup>(Note 5)</sup> | $E_{AS}$           | 250        | mJ         |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$     | -55 To 150 | $^\circ C$ |

**Thermal Characteristic**

|  |                 |      |               |
|--|-----------------|------|---------------|
| Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup> | $R_{\theta JC}$ | 2.27 | $^{\circ}C/W$ |
|--|-----------------|------|---------------|

**Electrical Characteristics ( $T_C=25^{\circ}C$  unless otherwise noted)**

| Parameter  | Symbol       | Condition  | Min | Typ  | Max       | Unit       |
|--|--------------|--|-----|------|-----------|------------|
| <b>Off Characteristics</b>                           |              |  |     |      |           |            |
| Drain-Source Breakdown Voltage                       | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$  | 100 | 110  | -         | V          |
| Zero Gate Voltage Drain Current                      | $I_{DSS}$    | $V_{DS}=100V, V_{GS}=0V$   | -   | -    | 1         | $\mu A$    |
| Gate-Body Leakage Current                            | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$  | -   | -    | $\pm 100$ | nA         |
| <b>On Characteristics</b> <sup>(Note 3)</sup>        |              |  |     |      |           |            |
| Gate Threshold Voltage                               | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$  | 1.2 | 1.8  | 2.5       | V          |
| Drain-Source On-State Resistance                     | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=5A$   | -   | 56   | 70        | m $\Omega$ |
| Forward Transconductance                             | $g_{FS}$     | $V_{DS}=50V, I_D=9A$   | 12  | -    | -         | S          |
| <b>Dynamic Characteristics</b> <sup>(Note 4)</sup>   |              |  |     |      |           |            |
| Input Capacitance                                    | $C_{iss}$    | $V_{DS}=25V, V_{GS}=0V,$<br>$F=1.0MHz$                               | -   | 1350 | -         | PF         |
| Output Capacitance                                   | $C_{oss}$    |  | -   | 240  | -         | PF         |
| Reverse Transfer Capacitance                         | $C_{riss}$   |  | -   | 180  | -         | PF         |
| <b>Switching Characteristics</b> <sup>(Note 4)</sup> |              |  |     |      |           |            |
| Turn-on Delay Time                                   | $t_{d(on)}$  | $V_{DD}=30V, I_D=2A, R_L=15\Omega$<br>$V_{GS}=10V, R_G=2.5\Omega$    | -   | 13.8 | -         | nS         |
| Turn-on Rise Time                                    | $t_r$        |  | -   | 9.3  | -         | nS         |
| Turn-Off Delay Time                                  | $t_{d(off)}$ |  | -   | 43.8 | -         | nS         |
| Turn-Off Fall Time                                   | $t_f$        |  | -   | 11.4 | -         | nS         |
| Total Gate Charge                                    | $Q_g$        | $V_{DS}=30V, I_D=3A,$<br>$V_{GS}=10V$                                | -   | 31   | -         | nC         |
| Gate-Source Charge                                   | $Q_{gs}$     |  | -   | 6.4  | -         | nC         |
| Gate-Drain Charge                                    | $Q_{gd}$     |  | -   | 9.4  | -         | nC         |
| <b>Drain-Source Diode Characteristics</b>            |              |  |     |      |           |            |
| Diode Forward Voltage <sup>(Note 3)</sup>            | $V_{SD}$     | $V_{GS}=0V, I_S=9A$  | -   | -    | 1.2       | V          |
| Diode Forward Current <sup>(Note 2)</sup>            | $I_S$        |  | -   | -    | 17        | A          |
| Forward Turn-On Time                                 | $t_{on}$     | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) |     |      |           |            |

**Notes:**

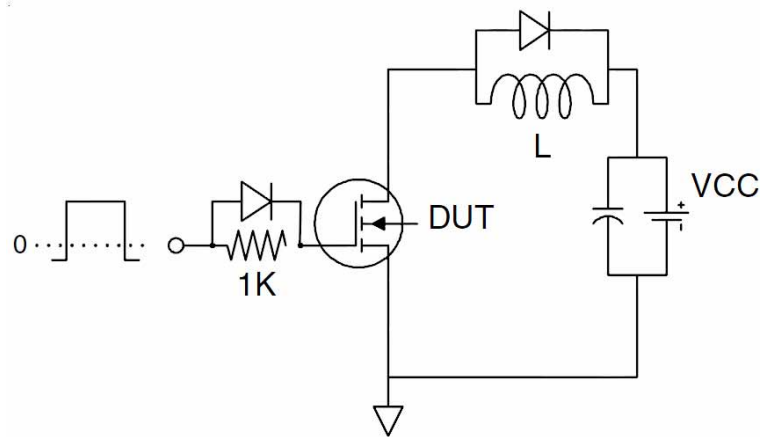
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_j=25^{\circ}C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

**Test Circuit**

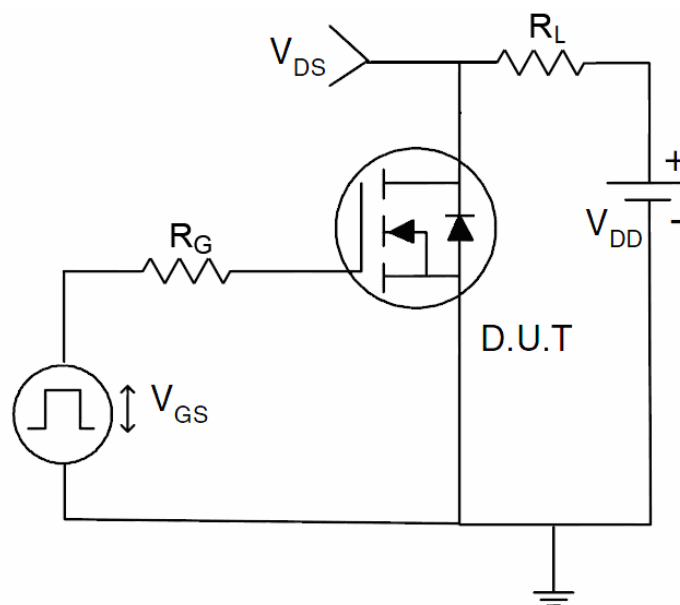
**1) E<sub>AS</sub> test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics (Curves)

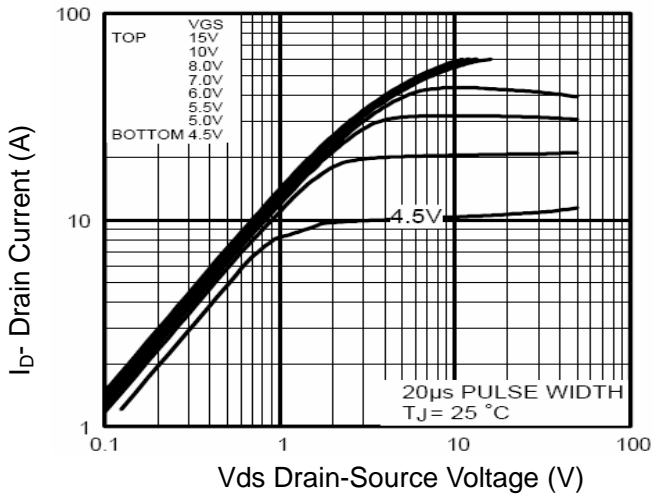


Figure 1 Output Characteristics

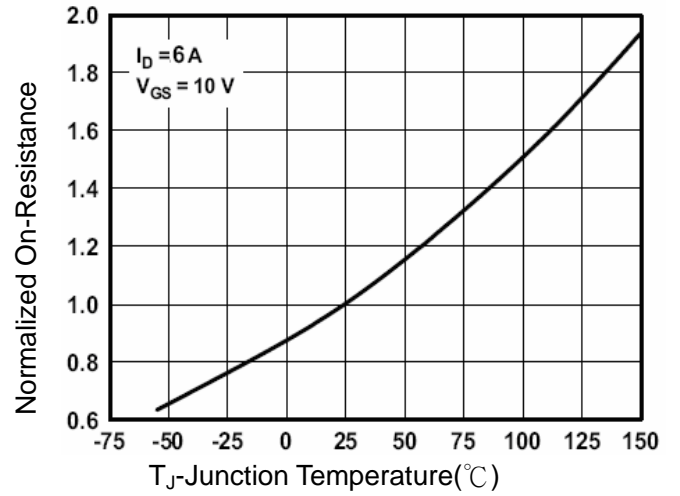


Figure 4 Rdson-Junction Temperature

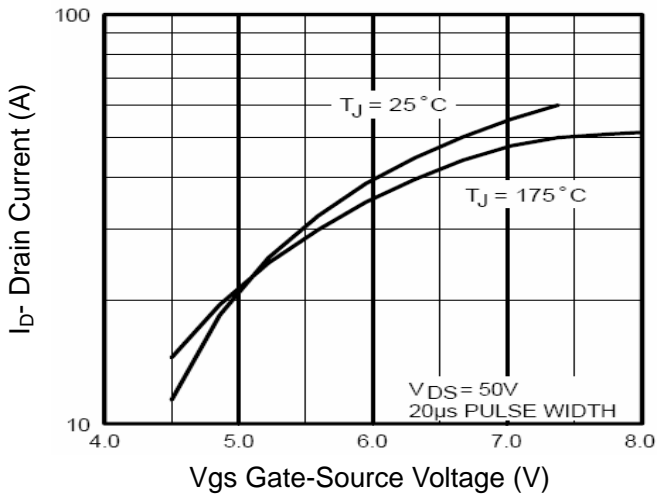


Figure 2 Transfer Characteristics

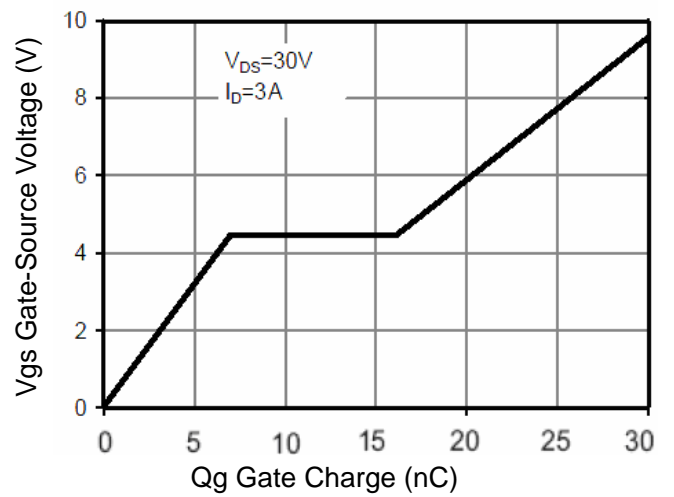


Figure 5 Gate Charge

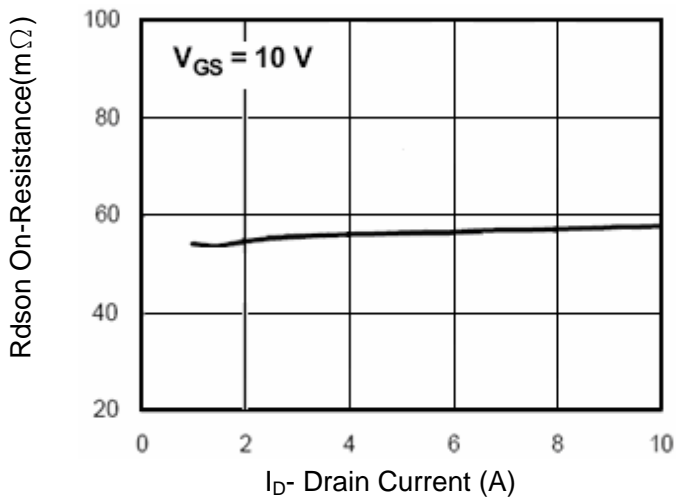


Figure 3 Rdson- Drain Current

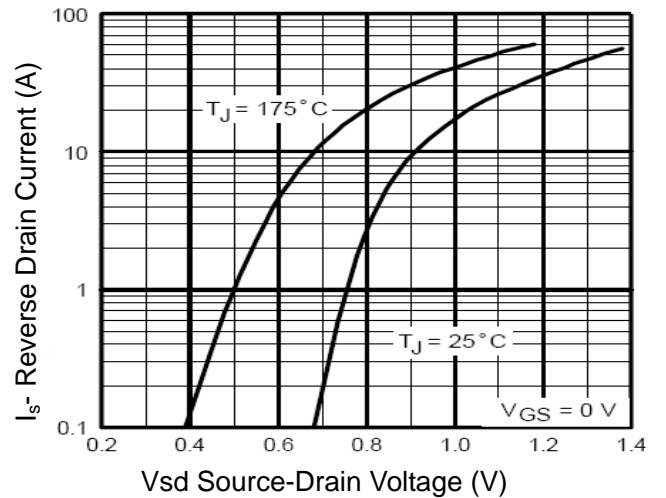


Figure 6 Source- Drain Diode Forward

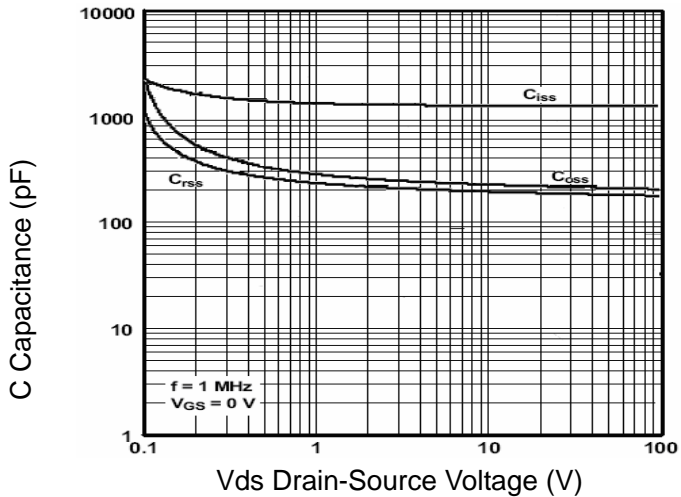


Figure 7 Capacitance vs Vds

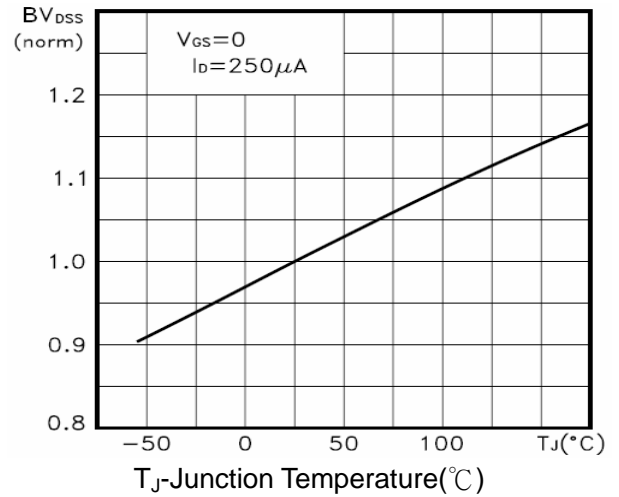


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

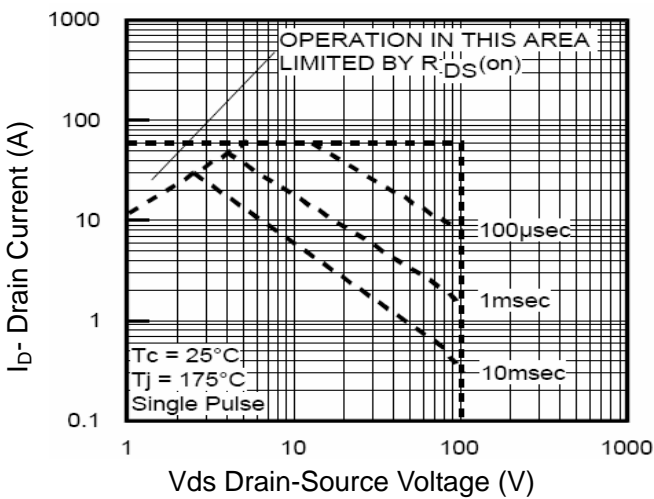


Figure 8 Safe Operation Area

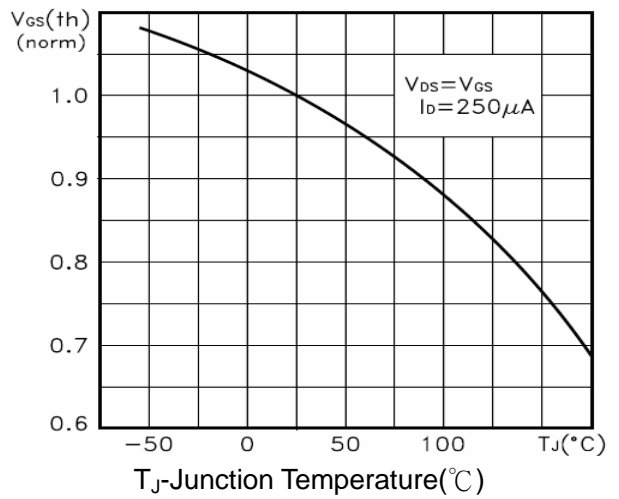


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

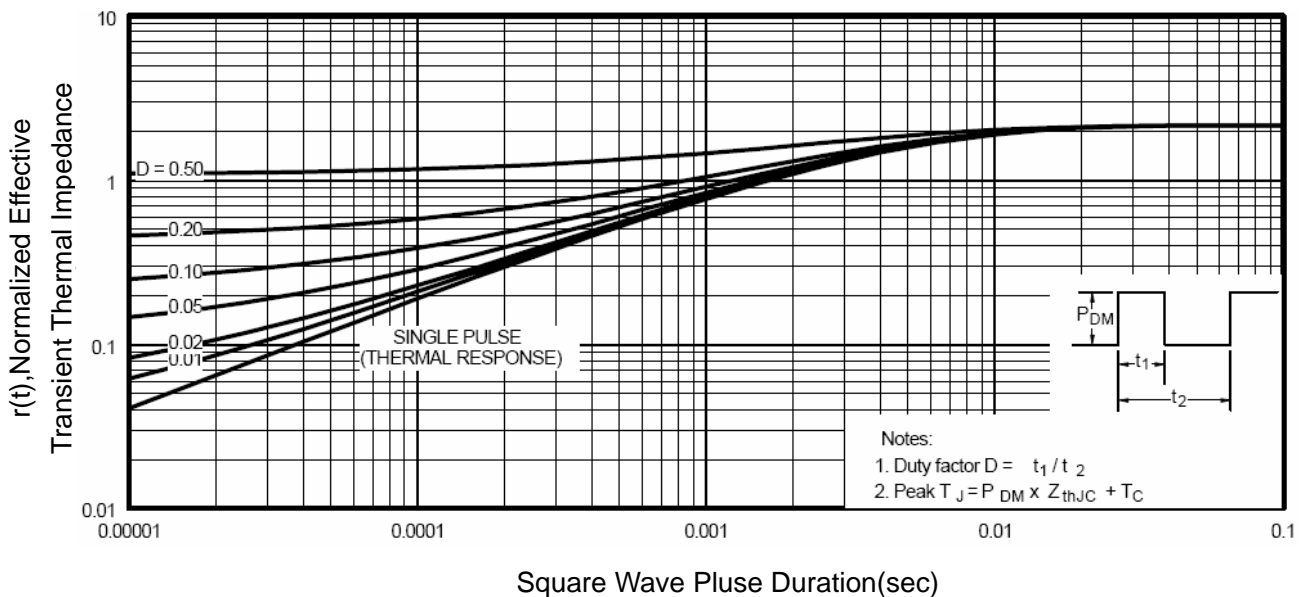
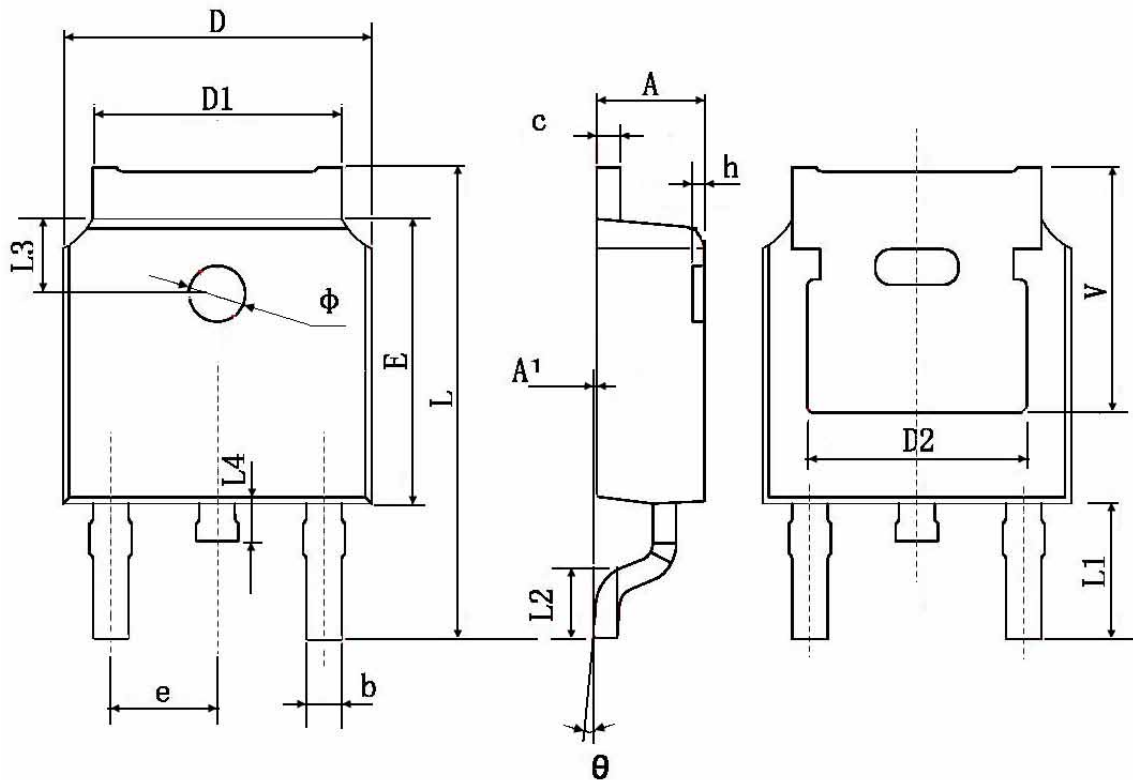


Figure 11 Normalized Maximum Transient Thermal Impedance

**TO-252 Package Information**



| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 2.200                     | 2.400  | 0.087                | 0.094 |
| A1     | 0.000                     | 0.127  | 0.000                | 0.005 |
| b      | 0.660                     | 0.860  | 0.026                | 0.034 |
| c      | 0.460                     | 0.580  | 0.018                | 0.023 |
| D      | 6.500                     | 6.700  | 0.256                | 0.264 |
| D1     | 5.100                     | 5.460  | 0.201                | 0.215 |
| D2     | 4.830 TYP.                |        | 0.190 TYP.           |       |
| E      | 6.000                     | 6.200  | 0.236                | 0.244 |
| e      | 2.186                     | 2.386  | 0.086                | 0.094 |
| L      | 9.800                     | 10.400 | 0.386                | 0.409 |
| L1     | 2.900 TYP.                |        | 0.114 TYP.           |       |
| L2     | 1.400                     | 1.700  | 0.055                | 0.067 |
| L3     | 1.600 TYP.                |        | 0.063 TYP.           |       |
| L4     | 0.600                     | 1.000  | 0.024                | 0.039 |
| Φ      | 1.100                     | 1.300  | 0.043                | 0.051 |
| θ      | 0°                        | 8°     | 0°                   | 8°    |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| V      | 5.350 TYP.                |        | 0.211 TYP.           |       |